

SiC - photodiode JEC 0,1SHT



- characteristics :**
- ◆ spectral range 210 ... 380 nm
 - ◆ active area 0,055 mm²
 - ◆ high UV-responsivity 0,13 A/W
 - ◆ TO 18-package
 - ◆ suitable for operating temperatures up to 150 °C

- applications :**
- ◆ UV-measurements only
 - ◆ UV-source control
 - ◆ flame detection

maximum ratings:

- reverse voltage 20 V
- operating temperature range -25 °C ... +150 °C
- storage temperature range -25 °C ... +150 °C
- soldering temperature (3s) 260 °C



technical data :

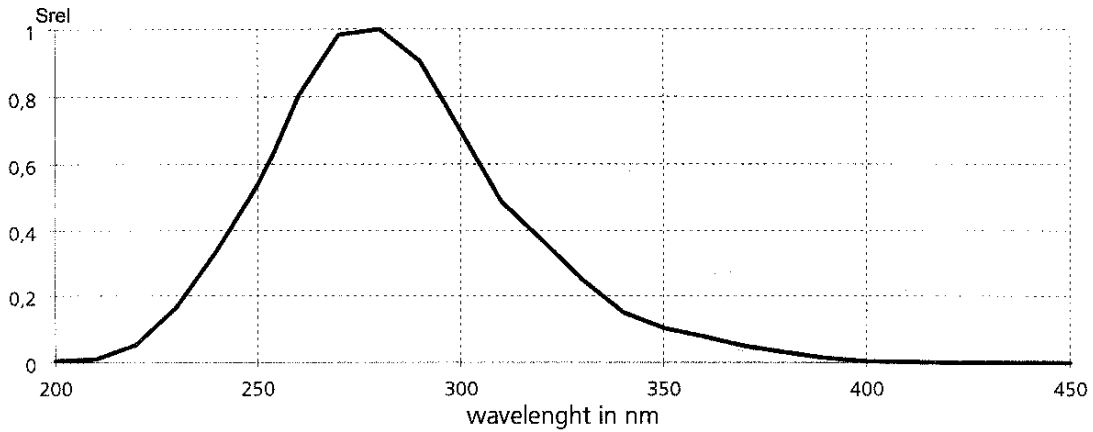
test conditions, as not otherwise specified: $\gamma_a = 25\text{ °C}$, $V_R = 0V$

parameter	test condition	min.	typ.	max.	unit
active area			0,25 x 0,25		mm ²
spectral range		210		380	nm
maximum of spectral responsivity	$\lambda_{max} = 275\text{ nm}$		0,13		A/W
absolute spectral responsivity	$\lambda = 254\text{ nm}$		0,11		A/W
dark current I_R	$V_R = 1\text{ V}$		1		fA
capacitance			21		pF

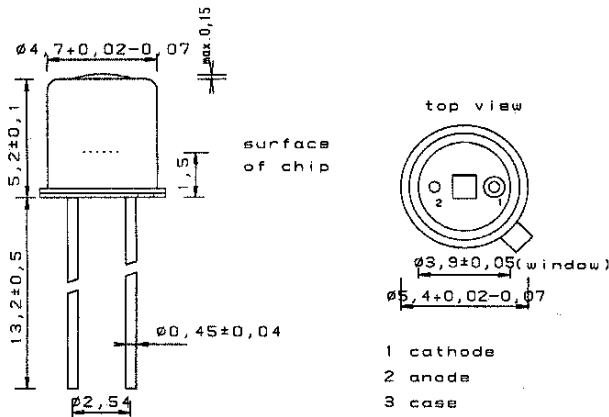
rev. 06/99

DATA SHEET

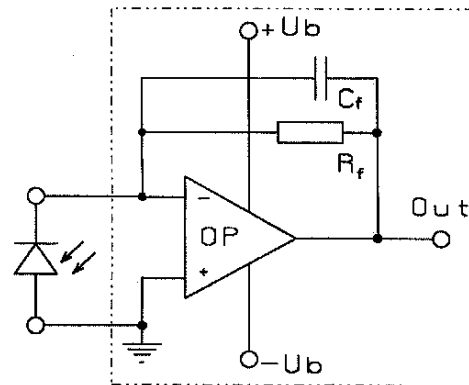
relative spectral responsivity



package dimensions

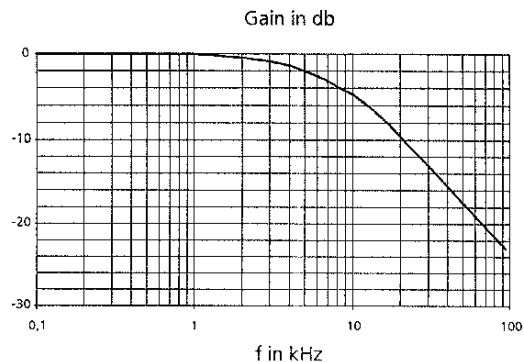


application example



The application example shows a typical circuit. R_f is responsible for the gain of the circuit. C_f compensates the reverse junction capacitance of the photodiode and input capacitance of the OPV. The exact value of C_f depends on R_f , used OPV and capacitance of the circuit. A typical value is 1 pF.

The diagram shows dependence of amplitude of the application circuit with OPA 111, $R_f = 50 \text{ M}\Omega$ and $C_f = 0.5 \text{ pF}$.



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